





Substitute for form 1449A&B/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary) OCT 17 2003 Sheet <u>1</u> of <u>1</u>		<b>Complete if Known</b>	
		Application Number	10/666 48 2
		Filing Date	9/18/03
		First Named Inventor	KOJI, YAMADA
		Art Unit	2883
		Examiner Name	ERIN CHIEF
		Attorney Docket Number	96790 P442

## U.S. PATENT DOCUMENT

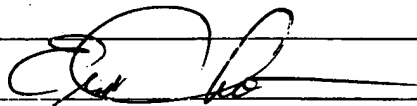
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US			
		US			
		US			

## FOREIGN PATENT DOCUMENT

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
efc		JP	10-122341	A	05-15-1998	HONDA MOTOR CO LTD	ABST
efc		JP	2002-122750	A	04-26-2002	NTT CORPORATION	ABST

## OTHER PRIOR ART—NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Translation <sup>6</sup>
efc		Shoji et al., "Optical International Structure of Si Waveguide on SOI Substrate", Extended Abstract (the 48 Spring Meeting, 2001) No.3, The Japan Society of Applied Physics and Related Societies (30a-YK-11)	
efc		Lee et al., "Fabrication of ultralow-loss Si/SiO <sub>2</sub> waveguides by roughness Reduction", OPTICS LETTERS, Vol. 26, NO. 23, December 1, 2001, Optical Society of America, pp. 1888 - 1890	
efc		Rickman et al., "Silicon-on-Insulator Optical Rib Waveguide Loss and Mode Characteristics", JOURNAL OF LIGHTWAVE TECHNOLOGY, VOL. 12, NO. 10, October 1994, IEEE, PP. 1771 - 1776	
efc		Lee et al., "Effect of size and roughness on light transmission in a Si/SiO <sub>2</sub> waveguide: Experiments and model", APPLIED PHYSICS LETTERS, VOLUME 77, NUMBER 11, 11 SEPTEMBER 2000, American Institute of Physics, pp. 1617 - 1619	
efc		Sakai et al., "Propagation Characteristics of Ultrahigh-Δ Optical Waveguide on Silicon-on Insulator Substrate", Jpn. J. Appl. Phys., Vol. 40, Part 2, No. 4B, 15 April 2001, pp. L383 - L385	
efc		Yamada et al., "SOI-based Photonic Crystal Line-Defect Waveguides", Invited Paper of Active and Passive Optical Components for WDM Communications II, Proceedings of SPIE, Vol. 4870 (2002)	

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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